



(11) **EP 0 906 896 B9**

(12) **CORRECTED EUROPEAN PATENT SPECIFICATION**

Note: Bibliography reflects the latest situation

(15) Correction information: **Corrected version no 1 (W1 B1)**  
**Corrections, see page(s) 3**

(51) Int Cl.: **C04B 35/52** (2006.01) **C04B 35/56** (2006.01)  
**F27B 9/04** (2006.01) **F27B 9/10** (2006.01)

(48) Corrigendum issued on:  
**14.03.2007 Bulletin 2007/11**

(45) Date of publication and mention  
of the grant of the patent:  
**26.04.2006 Bulletin 2006/17**

(21) Application number: **98203777.2**

(22) Date of filing: **04.02.1994**

(54) **Process for producing a dense, self-sintered silicon carbide/carbon-graphite composite**

Verfahren zum Herstellen eines dichten, selbstgesinterten Siliciumcarbid/Kohlenstoff-Graphitkomposit

Procédé de fabrication d'un composite dense et auto-fritté de carbure de silicium/carbone-graphite

(84) Designated Contracting States:  
**AT BE CH DE DK ES FR GB GR IE IT LI LU MC NL  
PT SE**

(30) Priority: **10.02.1993 US 17735**

(43) Date of publication of application:  
**07.04.1999 Bulletin 1999/14**

(62) Document number(s) of the earlier application(s) in  
accordance with Art. 76 EPC:  
**94909546.7 / 0 746 532**

(73) Proprietor: **THE MORGAN CRUCIBLE COMPANY  
PLC**  
**Windsor,**  
**Berkshire SL4 1LP (GB)**

(72) Inventors:  
• **Pfaff, Mark E.**  
**St. Marys,**  
**Pennsylvania 15857 (US)**  
• **Chen, Xin E.**  
**Crystal Lake,**  
**Illinois 60014 (US)**

(74) Representative: **Boff, James Charles et al**  
**Phillips & Leigh**  
**5 Pemberton Row**  
**London EC4A 3BA (GB)**

(56) References cited:  
**DE-A- 2 234 924** **DE-A- 3 329 225**  
**US-A- 4 525 461** **US-A- 4 690 909**  
**US-A- 4 692 418** **US-A- 5 135 893**

- **CHEMICAL ABSTRACTS, vol. 110, no. 18, 1 May 1989 Columbus, Ohio, US; abstract no. 159286, XP002032824 & JP 63 260861 A (BROTHER IND., LTD.) 27 October 1988**
- **CHEMICAL ABSTRACTS, vol. 110, no. 20, 15 May 1989 Columbus, Ohio, US; abstract no. 178331, XP002032825 & JP 63 265850 A (BROTHER IND., LTD.) 2 November 1988**
- **CHEMICAL ABSTRACTS, vol. 108, no. 18, 2 May 1988 Columbus, Ohio, US; abstract no. 155356, XP002032826 & JP 63 011559 A (BROTHER IND., LTD.) 19 January 1988**

Note: Within nine months from the publication of the mention of the grant of the European patent, any person may give notice to the European Patent Office of opposition to the European patent granted. Notice of opposition shall be filed in a written reasoned statement. It shall not be deemed to have been filed until the opposition fee has been paid. (Art. 99(1) European Patent Convention).

**EP 0 906 896 B9**

## Description

### FIELD OF THE INVENTION

**[0001]** This invention relates to the field of silicon carbide and graphite composite materials and more particularly to a process for producing dense, self-sintered silicon carbide and graphite composite materials.

### BACKGROUND OF THE INVENTION

**[0002]** Silicon carbide is hard, strong, and exhibits good corrosion and abrasion resistance and high thermal conductivity. It can be used in oxidizing temperatures up to 2500°F. These properties render silicon carbide a useful material in many acid, caustic, corrosive, abrasive, or high temperature environments. Such applications include pump seals and bearings, gas turbine components, mixing nozzles, and flame holders.

**[0003]** Silicon carbide bodies are frequently formed by a sintering process. Sintered silicon carbide has a high hardness, good corrosion resistance, and high thermal conductivity. In sintering, particles of a material bond together when heated to a high temperature, below the material's melting point. In some processes, the material is also subjected to high pressure as well. A self-sintered process is one which does not require application of pressure during the heating step for sintering to occur.

**[0004]** A drawback to silicon carbide is its lack of self-lubricity. A self-lubricating solid is one having low friction in the absence of an additional lubricant. For example, in applications having a high PV (pressure-sliding velocity) limit or dry running applications, parts, such as seals, having a silicon carbide face adjoining a face made of silicon carbide, other ceramics, or steel, will wear excessively due to the forces generated by the high friction. In dry running applications with mating surfaces, special wear surfaces must be provided on at least one of the bodies.

**[0005]** Graphite is a known lubricant and has been incorporated into carbon and silicon carbide materials to impart a self-lubricating property to the material. However, with sintered materials, it has been difficult to incorporate large amounts of a second phase such as graphite into a ceramic matrix without causing cracks to occur in the microstructure or without increasing the material's porosity. Further, adding graphite to silicon carbide is even more difficult, because sintering of silicon carbide already requires stringent conditions, such as fine, high purity powders, sintering aids, and high temperature.

**[0006]** It is known to form a silicon carbide and graphite material by reaction bonding or reaction sintering. However, reaction-bonded silicon carbide and graphite material typically has a residual silicon phase which limits corrosion resistance due to reaction with the silicon in some chemical applications. Also, controlling the reaction bonding process to obtain fully reacted and fully dense parts is difficult.

**[0007]** Another known silicon carbide material incorporating graphite is disclosed in U.S. Patent No. 4,525,461. This material comprises a sintered silicon carbide graphite and carbon composite ceramic body having a homogeneous fine grain microstructure. At least 50% of the silicon carbide grains are less than 8  $\mu\text{m}$ , and the graphite grains have an average size no larger than that of the silicon carbide grains. However, if the amount of graphite is greater than approximately 8% by weight in this material, the material's density decreases. Less than 8% by weight graphite, while providing a more dense, impervious structure, limits the graphite's lubricating capability in the material.

**[0008]** Thus, there exists a need for a process for producing a dense, impervious self-sintered silicon carbide body with a greater amount of graphite inclusions to increase the lubricity of the material while maintaining the integrity of the microstructure.

**[0009]** The present invention provides a process for producing a dense, self-sintered silicon carbide and carbon-graphite composite material comprising the steps of:

(a) providing a particulate mixture comprising:

- (i) carbon-bonded graphite of between 2 and 30 percent by weight of the mixture, the carbon-bonded graphite comprising at least 5 percent by weight carbon-precursor binder, the balance being graphite,
- (ii) between 1 and 10 percent by weight of a binder,
- (iii) between 0.1 and 15 percent of a sintering aid,
- (iv) between 1 and 5 percent by weight of a lubricant, and
- (v) the balance being silicon carbide; and

(b) shaping the mixture to form a green body;

(c) heating the green body in a non-oxidising atmosphere at a carbonizing temperature above 371°C (700°F) to carbonize the binder; and

(d) sintering the carbonized body at a temperature ranging from 1900°C to 2300°C in a substantially inert atmosphere at or below atmospheric pressure to produce a sintered body having a density of at least 80 percent of theoretical and a microstructure in which the average grain size of the carbon-graphite is larger than the average grain size of the silicon carbide.

**[0010]** The silicon carbide may comprise  $\alpha$ -silicon carbide,  $\beta$ -silicon carbide, or a combination of both

### DESCRIPTION OF THE DRAWINGS

**[0011]** The invention will be more fully understood from the following detailed description taken in conjunction with the accompanying drawings in which:

Fig. 1 is a schematic illustration of the process according to the present invention for producing a dense, self-sintered silicon carbide and carbon-graphite composite material;

Fig. 2 is a table of test results;

Fig. 3 is an optical photomicrograph at 50X magnification of a silicon carbide and carbon-graphite composite material obtained according to the process of the present invention;

Fig. 4 is a further optical photomicrograph at 50X magnification of a silicon carbide and carbon-graphite composite material obtained according to the process of the present invention; and

Figs. 5a, 5b, 5c, and 5d are scanning electron micrographs at 50X, 500X, 1000X, and 2000X magnification respectively, of a further silicon carbide and carbon-graphite composite material obtained according to the process of the present invention.

**[0012]** The process of the present invention for producing the dense, self-sintered composite material is shown schematically in Fig. 1. The composite body is formed from a particulate mixture of a silicon carbide matrix formulation and a carbon-bonded graphite. The carbon binder for the graphite comprises a carbon-precursor resin capable of leaving a carbon residue upon heating, to be described more fully below.

**[0013]** The silicon carbide matrix formulation may comprise a fine-grained, high purity  $\alpha$ -silicon carbide,  $\beta$ -silicon carbide, or a combination thereof. Preferably, at least 0.5 percent  $\alpha$ -silicon carbide relative to  $\beta$ -silicon carbide is present to achieve better densification. A formulation comprising approximately 90 to 91 percent  $\beta$ -SiC, 4 to 5 percent  $\alpha$ -sic, and 5 percent resin binder has been found to provide satisfactory results. The  $\alpha$ -SiC and  $\beta$ -sic may be supplied from any commercially available source.

**[0014]** Generally, a slurry of  $\alpha$ -SiC and  $\beta$ -SiC in distilled water is prepared. The SiC is typically provided in powder form and should be fine-grained, having a BET surface area of more than 5 m<sup>2</sup>/g and preferably more than 10 m<sup>2</sup>/g. Also, the powder should be of a high purity, generally at least 95 percent and preferably 97 percent pure. Typically, a sintering aid, such as boron or boron carbide, B<sub>4</sub>C, is added to the SiC suspension. Other known sintering aids, such as aluminum or beryllium or compounds thereof; may be provided if desired. Alternatively, a sintering aid may be introduced at other known steps in the process of forming a sintered composite body. A dispersant, for example, ammonium polymethacrylate, is generally added to the slurry. The dispersant is a temporary additive not forming part of the final composite body. The slurry is mixed, for example, in a ball mill for a period of time, typically about eight hours, sufficient to disperse the ingredients. The slurry is then transferred to a mixing tank.

**[0015]** The carbon-bonded graphite is prepared for addition to the SiC slurry. It comprises at least 5 percent by

weight of a carbon binder, the balance comprising a coarse graphite. In the preferred embodiment, a mixture of approximately 70 to 80 percent graphite and 20 to 30 percent binder is provided. A greater amount of binder may be used, although the lubricating capability of the graphite in the final composite body may be reduced.

**[0016]** A coarse graphite such as Lonza KS-150, available from Lonza, Inc., Fairlawn, NJ, in which 55 percent of the particles are larger than 45  $\mu$ m, is suitable. A suitable binder is a phenolic resin, although other materials which will decompose upon heating to leave a carbon residue, such as furfuryl alcohol, polyester resin, coal tar pitch, or mixtures of these and other materials, may be used. Upon decomposition, the binder causes an increase in the porosity of the graphite particles, as discussed further below.

**[0017]** The binder in powdered form is dissolved in acetone or any other suitable solvent and mixed thoroughly with the graphite to bond the graphite particles. The mixture is dried to evaporate the solvent and crushed to obtain carbon-bonded graphite particles of the desired size. Preferably, the carbon-bonded graphite is passed through a 200-mesh sieve to obtain particles of less than 75  $\mu$ m. The carbon-bonded graphite is then added to the mixing tank with the SiC slurry. The carbon-bonded graphite generally comprises between 2 and 30 percent by weight of the solids content of the mixture.

**[0018]** A resin solution in distilled water is also added to the mixing tank as a binder for subsequent shaping of the particulate mixture to form a green body. The resin, for example, phenolic resin, typically comprises 5 percent of the total SiC matrix formulation. Also, a die lubricant, such as oleic acid, is generally added in an amount equal to approximately 5 percent of the total SiC matrix formulation (SiC and resin binder). The die lubricant, which is also a temporary additive not forming a part of the final composite body, facilitates subsequent removal from the die in which the particulate mixture is shaped.

**[0019]** The resulting slurry is mixed thoroughly and dried. Typically, the slurry is spray dried to form spherical granules having an average size less than approximately 500  $\mu$ m. Any other suitable methods for obtaining such granules may be used. For example, the slurry may be pan dried, crushed to obtain a flour, and passed through a sieve to obtain the desired particle size.

**[0020]** A measured amount of the particulate mixture is fed into a die and compacted, typically at pressures ranging between 2 to 20 tons/in<sup>2</sup>, to the desired shape to form a green body. Any other suitable method of shaping the mixture may be employed. The shaped green body is carbonized in a non-oxidizing atmosphere above 700°F. In a typical carbonization cycle, the component is heated in an oven from room temperature to 350°F during a half hour period and allowed to soak at that temperature for another half hour. The temperature is raised to 850°F over a period of ten hours and held at 850°F for five hours to carbonize the resin. The component is then cooled to room temperature. Other suitable carboniza-

tion cycles may be used.

**[0021]** Next, the carbonized body is sintered at a temperature ranging from 1900°C to 2300°C, preferably 2000°C to 2200°C, in a substantially inert atmosphere such as helium or argon at or below atmospheric pressure. Generally, the temperature is raised to the sintering temperature over an eight hour period, although the actual time depends on the particular furnace used. The furnace is held at the peak temperature for one hour and then allowed to cool to room temperature. Other suitable sintering cycles may be used. Additionally, the carbonization cycle and the sintering cycle may be carried out in separate furnaces or in a single furnace.

**[0022]** The process of the present invention results in a sintered composite body comprising between 55 and 97.9 percent by weight silicon carbide, between 2 and 30 percent by weight carbon-graphite, and between 0.1 and 15 percent by weight sintering aids. The material has a density of at least 80 percent, and preferably 90 percent, of the theoretical density of the particular mixture. This density may be achieved, since during carbonization, part of the carbon-precursor binder for the graphite volatilizes, leaving voids, while the remainder forms a coke residue on the graphite. Thus, the carbon-graphite particles at this stage have a greater porosity than graphite alone. Subsequently during sintering, the porous carbon-graphite collapses, allowing greater shrinkage of the SiC matrix despite the presence of the carbon-graphite inclusions. Thus, a relatively dense and impervious composite body results. The resulting composite body has a microstructure in which the average grain size of the carbon-graphite is larger than the average grain size of the silicon carbide. The average grain size of the carbon-graphite ranges between 10 and 75  $\mu\text{m}$ , and the average grain size of the silicon carbide ranges between 2 and 15  $\mu\text{m}$ . Preferably, the carbon-graphite has an average grain size between 20 and 30  $\mu\text{m}$ .

**[0023]** Tests of several different compositions were performed according to the process of the present invention. See Fig. 2. In test bake nos. 1-17, the silicon carbide matrix was provided by a mix consisting of 90.25 percent of a fine-grained  $\beta$ -SiC powder having a BET surface area of 13.5 to 18.5  $\text{m}^2/\text{g}$ , 4.75 percent of a fine-grained  $\alpha$ -SiC having a BET surface area of 9.0 to 11.0  $\text{m}^2/\text{g}$ , and 5.0 percent liquid phenolic resin. In test bake no. 18, the silicon carbide matrix was provided by 100 percent  $\alpha$ -SiC having a BET surface area of 15  $\text{m}^2/\text{g}$ .  $\text{B}_4\text{C}$  was used as a sintering aid, comprising approximately one percent of the total mix. Oleic acid was added as a die lubricant in an amount comprising approximately 5.0 percent of the total mix. These components are readily available from known commercial sources.

**[0024]** Several grades of graphite were tested to determine which provided the best sinterability: a fine graphite in which 50 percent of the particles are smaller than 2.4  $\mu\text{m}$ , a coarse graphite in which 55 percent of the particles are larger than 45  $\mu\text{m}$ , and a coarse, resin-bonded graphite in which 50 percent of the particles are

larger than 74  $\mu\text{m}$ . The fine graphite used in the tests was Lonza KS-6, commercially available from Lonza, Inc. The coarse graphite used was Lonza KS-150, also commercially available from Lonza, Inc. The coarse, carbon-bonded graphite was specially mixed as described above and consisted of 20 percent by weight phenolic resin and 80 percent by weight Lonza KS-150.

**[0025]** In the tests, the composite body was formed by mixing a slurry of the silicon carbide with the graphite or carbon-bonded graphite. The mixture was dried and granulated and molded at 2 to 20 tons per square inch. The molded green body was carbonized at 850°F, and the carbonized body was sintered at temperatures of 2070°C and 2090°C.

**[0026]** Test results are shown in Fig. 2. In some test bakes, the graphite was sieved prior to mixing with the silicon carbide to obtain a specific size range. This is indicated in the column "Graphite Size." The entry "Un-sized" indicates that the graphite was not sieved. The sieved graphite is indicated by the appropriate size ranges. The specially mixed carbon-bonded graphite is designated Mix No. 1 in the column labeled "Graphite Type."

**[0027]** The tests show that samples containing large amounts of the commercially available non-carbon-bonded graphites, i.e., the fine graphite, Lonza KS6, and the coarse graphite, Lonza KS150, (Test Bake Nos. 3-8) did not provide satisfactory results. The resulting sintered samples were too porous, as indicated by the percent of water absorption, and did not achieve sufficient densification.

**[0028]** The samples using the specially mixed coarse, carbon-bonded graphite (Test Bake Nos. 9-17) indicate that greater densification was achieved with a graphite loading of 15 percent by weight than has been achieved in prior art composite bodies using a comparable loading of non-carbon-bonded graphite. Some lamination in removal from the die, leading to some water absorption, occurred using the larger graphite particles. Lamination did not occur when carbon-bonded graphite particles small enough to pass through the 200-mesh sieve, that is, less than 75  $\mu\text{m}$ , were used.

**[0029]** Silicon carbide and carbon-graphite, composite materials obtained according to the process of the present invention are shown in the photomicrographs of Figs. 3 through 5. The carbon-graphite appears as the darker inclusions among the lighter silicon carbide matrix. Fig. 3 shows an optical micrograph of a polished cross-section of test bake no. 11 magnified 50 times (50X). The material appears fully dense and the carbon-graphite is uniformly distributed.

**[0030]** Fig. 4 shows an optical micrograph of a polished cross-section of test bake no. 17 at 50X magnification. The material appears fully dense and the carbon-graphite is uniformly distributed.

**[0031]** Figs. 5a through 5d show scanning electron micrographs at 50X, 500X, 1000X, and 2000X magnification respectively of test bake no. 17 polished and etched to show the grain structure. The grain size of the silicon

carbide, is less than 10  $\mu\text{m}$ , and the carbon-graphite grain size is in the range of 20 to 60  $\mu\text{m}$ .

[0032] The invention is not to be limited by what has been particularly shown and described, except as indicated in the appended claims.

## Claims

1. A process for producing a dense, self-sintered silicon carbide and carbon-graphite composite material comprising the steps of:

(a) providing a particulate mixture comprising:

- (i) carbon-bonded graphite of between 2 and 30 percent by weight of the mixture, the carbon-bonded graphite comprising at least 5 percent by weight carbon-precursor binder, the balance being graphite,
- (ii) between 1 and 10 percent by weight of a binder,
- (iii) between 0.1 and 15 percent of a sintering aid,
- (iv) between 1 and 5 percent by weight of a lubricant, and
- (v) the balance being silicon carbide; and

(b) shaping the mixture to form a green body;  
 (c) heating the green body in a non-oxidising atmosphere at a carbonizing temperature above 371°C (700°F) to carbonize the binder; and  
 (d) sintering the carbonized body at a temperature ranging from 1900°C to 2300°C in a substantially inert atmosphere at or below atmospheric pressure to produce a sintered body having a density of at least 80 percent of theoretical and a microstructure in which the average grain size of the carbon-graphite is larger than the average grain size of the silicon carbide.

2. The process of claim 1, wherein the carbon-precursor binder comprises phenolic resin, furfuryl alcohol resin, polyester resin, coal tar pitch, or mixtures thereof.

3. The process of claim 1 or claim 2, wherein the carbonized body is sintered at a temperature ranging from 2100°C to 2200°C.

4. The process of any preceding claim, wherein the carbon-bonded graphite has a particle size less than 75  $\mu\text{m}$ .

5. The process of any preceding claim, wherein the silicon carbide comprises at least 0.5 percent by weight  $\alpha$ -silicon carbide, the balance being  $\beta$ -silicon carbide.

6. The process of any preceding claim, wherein the carbon-bonded graphite comprises between 20 and 30 percent by weight carbon-precursor resin and between 70 and 80 percent by weight graphite.

7. The process of any preceding claim, wherein the silicon carbide comprises 95 percent by weight  $\beta$ -silicon carbide and 5 percent by weight  $\alpha$ -silicon carbide.

8. The process of any preceding claim, wherein the silicon carbide has a BET surface area less than 50  $\text{m}^2/\text{g}$ .

9. The process of any preceding claim, wherein the silicon carbide has a BET surface area less than 20  $\text{m}^2/\text{g}$ .

10. The process of any preceding claim, wherein the carbon-bonded graphite is prepared by providing a mixture of a coarse graphite and a carbon-precursor binder dissolved in a solvent, drying the mixture and crushing to obtain particles of less than 75  $\mu\text{m}$ .

## Revendications

1. Procédé de production d'un matériau composite de carbure de silicium et carbone-graphite, auto-fritté, dense, comprenant les étapes suivantes :

(a) fournir un mélange particulaire comprenant :

- (i) du graphite lié par du carbone représentant 2 à 30 pour cent en poids du mélange, le graphite lié par du carbone comprenant au moins 5 pour cent en poids de liant précurseur de carbone, le reste étant du graphite,
- (ii) entre 1 et 10 pour cent en poids d'un liant,
- (iii) entre 0,1 et 15 pour cent en poids d'un adjuvant de frittage,
- (iv) entre 1 et 5 pour cent en poids d'un lubrifiant, et
- (v) le reste étant du carbure de silicium ; et

(b) façonner le mélange pour former un corps cru ;

(c) chauffer le corps cru dans une atmosphère non oxydante à une température de carbonisation supérieure à 371°C (700°F) pour carboniser le liant ; et

(d) fritter le corps carbonisé à une température comprise entre 1900°C et 2300°C dans une atmosphère sensiblement inerte à une pression égale ou inférieure à la pression atmosphérique pour produire un corps fritté ayant une densité d'au moins 80 pour cent de la théorie et une

- microstructure dans laquelle la taille moyenne des grains du carbone-graphite est supérieure à la taille moyenne des grains du carbure de silicium.
2. Procédé selon la revendication 1, dans lequel le liant précurseur de carbone comprend une résine phénolique, une résine d'alcool furfurylique, une résine polyester, du brai de goudron de houille, ou des mélanges d'entre eux.
3. Procédé selon la revendication 1 ou la revendication 2, dans lequel le corps carbonisé est fritté à une température comprise entre 2100°C et 2200°C.
4. Procédé selon l'une quelconque des revendications précédentes, dans lequel le graphite lié par du carbone a une taille de particule inférieure à 75 µm.
5. Procédé selon l'une quelconque des revendications précédentes, dans lequel le carbure de silicium comprend au moins 0,5 pour cent en poids de carbure de silicium α, le reste étant du carbure de silicium β.
6. Procédé selon l'une quelconque des revendications précédentes, dans lequel le graphite lié par du carbone comprend entre 20 et 30 pour cent en poids de résine précurseur de carbone et entre 70 et 80 pour cent en poids de graphite.
7. Procédé selon l'une quelconque des revendications précédentes, dans lequel le carbure de silicium comprend 95 pour cent en poids de carbure de silicium β et 5 pour cent en poids de carbure de silicium α.
8. Procédé selon l'une quelconque des revendications précédentes, dans lequel le carbure de silicium a une surface spécifique BET inférieure à 50 m<sup>2</sup>/g.
9. Procédé selon l'une quelconque des revendications précédentes, dans lequel le carbure de silicium a une surface spécifique BET inférieure à 20 m<sup>2</sup>/g.
10. Procédé selon l'une quelconque des revendications précédentes, dans lequel le graphite lié par du carbone est préparé en formant un mélange d'un graphite grossier et d'un liant précurseur de carbone dissous dans un solvant, en séchant le mélange et en le broyant pour obtenir des particules de moins de 75 µm.
- (a) Bereitstellen einer aus Teilchen bestehenden Mischung enthaltend:
- (i) an Kohlenstoff gebundenen Graphit zu zwischen 2 und 30 Gewichtsprozent der Mischung, wobei der an Kohlenstoff gebundene Graphit mindestens 5 Gewichtsprozent eines Kohlenstoffvorläufer-Bindemittels enthält und Graphit die Restmenge darstellt,
- (ii) zwischen 1 und 10 Gewichtsprozent eines Bindemittels,
- (iii) zwischen 0,1 und 15 Prozent eines Sinterhilfsmittels,
- (iv) zwischen 1 und 5 Gewichtsprozent eines Schmiermittels, und
- (v) wobei die verbleibende Menge Siliciumcarbid darstellt; und
- (b) Formen der Mischung, um einen Grünkörper auszubilden;
- (c) Erhitzen des Grünkörpers in einer nicht oxidierenden Atmosphäre bei einer Karbonisierungstemperatur oberhalb von 371 °C (700 °F), um das Bindemittel zu karbonisieren; und
- (d) Sintern des karbonisierten Körpers bei einer Temperatur im Bereich von 1900 °C bis 2300 °C in einer im wesentlichen inerten Atmosphäre bei oder unterhalb von Atmosphärendruck, um einen gesinterten Körper herzustellen, der eine Dichte von mindestens 80 Prozent der theoretischen Dichte sowie eine Mikrostruktur aufweist, in der die mittlere Korngröße des Kohlenstoff-Graphits größer als die mittlere Korngröße des Siliciumcarbids ist.
2. Verfahren nach Anspruch 1, wobei das Kohlenstoffvorläufer-Bindemittel Phenolharz, Furfurylalkoholharz, Polyesterharz, Steinkohlenteerpech oder Mischungen daraus enthält.
3. Verfahren nach Anspruch 1 oder Anspruch 2, wobei der karbonisierte Körper bei einer Temperatur im Bereich von 2100 °C bis 2200 °C gesintert wird.
4. Verfahren nach irgendeinem der vorhergehenden Ansprüche, wobei der an Kohlenstoff gebundene Graphit eine Teilchengröße von weniger als 75 µm aufweist.
5. Verfahren nach irgendeinem der vorhergehenden Ansprüche, wobei das Siliciumcarbid mindestens 0,5 Gewichtsprozent α-Siliciumcarbid enthält, wobei die verbleibende Menge β-Siliciumcarbid ist.
6. Verfahren nach irgendeinem der vorhergehenden Ansprüche, wobei der an Kohlenstoff gebundene Graphit zwischen 20 und 30 Gewichtsprozent Koh-

### Patentansprüche

1. Verfahren zur Herstellung eines dichten, selbstgesinterten Siliciumcarbid- und Kohlenstoff-Graphit-Verbundwerkstoffes, umfassend die Schritte:

lenstoffvorläuferharz und zwischen 70 und 80 Gewichtsprozent Graphit enthält.

7. Verfahren nach irgendeinem der vorhergehenden Ansprüche, wobei das Siliciumcarbid 95 Gewichtsprozent  $\beta$ -Siliciumcarbid enthält und 5 Gewichtsprozent  $\alpha$ -Siliciumcarbid. 5
8. Verfahren nach irgendeinem der vorhergehenden Ansprüche, wobei das Siliciumcarbid eine BET-Oberfläche von weniger als 50 m<sup>2</sup>/g besitzt. 10
9. Verfahren nach irgendeinem der vorhergehenden Ansprüche, wobei das Siliciumcarbid eine BET-Oberfläche von weniger als 20 m<sup>2</sup>/g besitzt. 15
10. Verfahren nach irgendeinem der vorhergehenden Ansprüche, wobei der an Kohlenstoff gebundene Graphit hergestellt wird durch Bereitstellen einer Mischung eines groben Graphits und eines Kohlenstoffvorläufer-Bindemittels, das in einem Lösungsmittel gelöst ist, Trocknen der Mischung und Zermahlen, um Teilchen von weniger als 75  $\mu$ m zu erhalten. 20

25

30

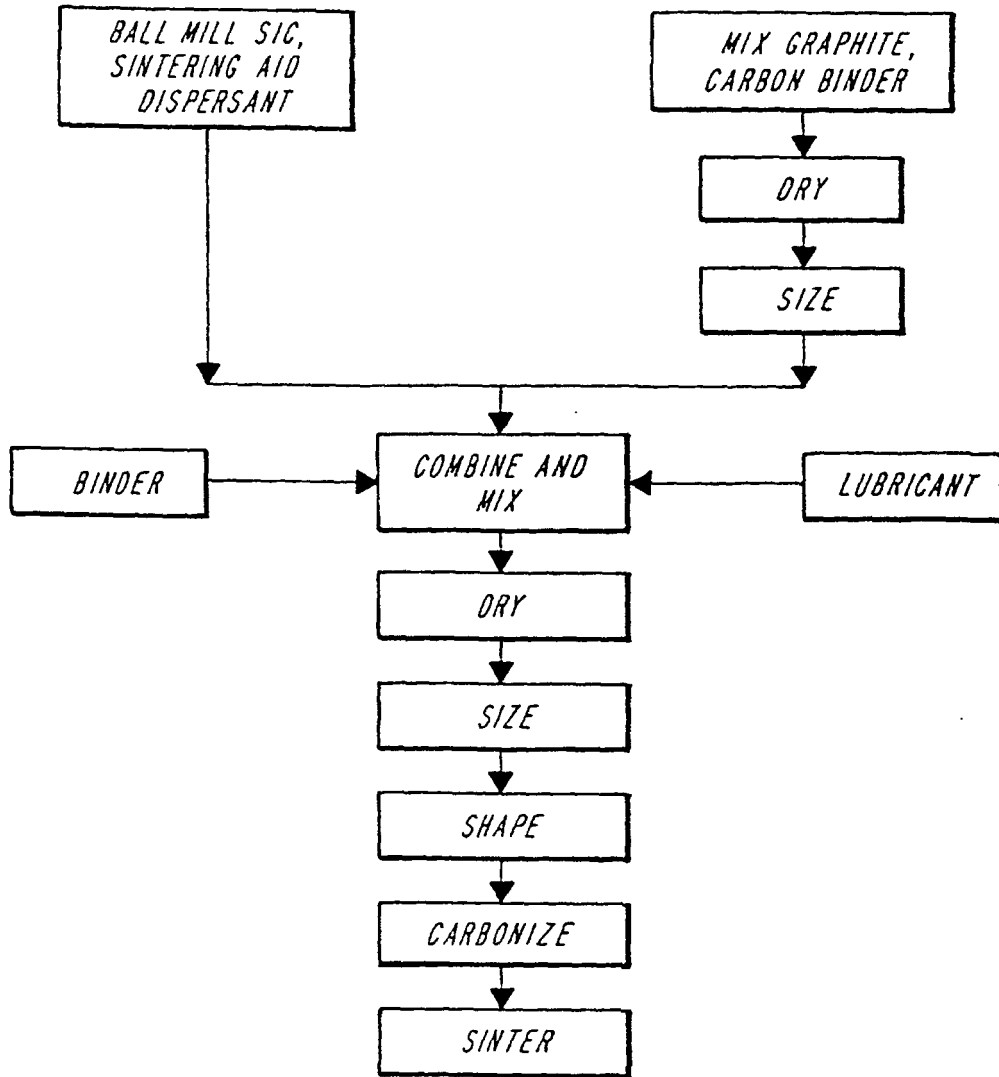
35

40

45

50

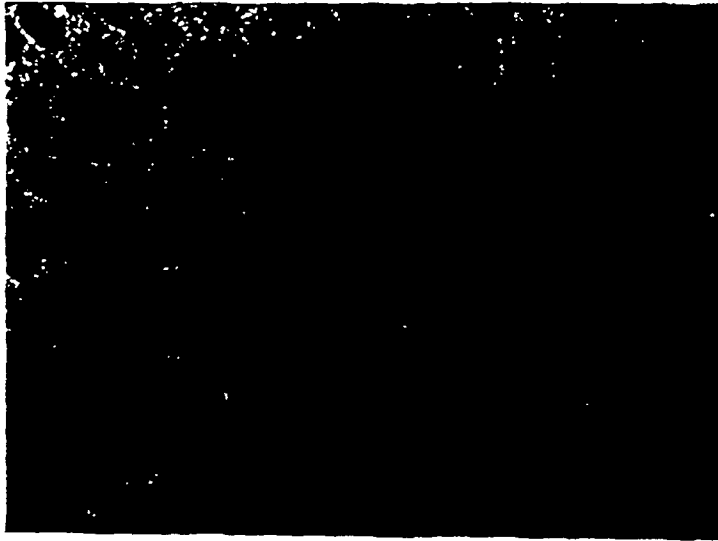
55



*FIG. 1*

TEST BAKE N <sup>o</sup>	GRAPHITE WT.%	GRAPHITE SOURCE	GRAPHITE SIZE	SIC FORMULATION	SINTERING TEMP. DEG. C	FINAL DENSITY G/CC	WATER ABSORPTION %	REMARKS
1	4.6%	KS6	UNSIZED	90.25% $\beta$ -SIC 4.75% $\alpha$ -SIC	2070	2.95	0.12%	
2	8.7%	KS6	UNSIZED	-	2070	2.79	1.48%	
3	16.0%	KS6	UNSIZED	-	2070	2.56	4.80%	
4	22.2%	KS6	UNSIZED	-	2070	2.28	8.59%	
5	15%	KS150	-70, +100 MESH	-				UNABLE TO HOLD, LAMINATION
6	15%	KS150	-100, +200 MESH	-				UNABLE TO HOLD, LAMINATION
7	15%	KS150	-200, +325 MESH	-	2090	2.45	6.02%	
8	15%	KS150	-325 MESH	-	2090	2.49	5.00%	
9	4.6%	MIX NO. 1	UNSIZED	-	2070	3.03	0	
10	8.7%	MIX NO. 1	UNSIZED	-	2070	2.83	1.18%	LAMINATION
11	16.0%	MIX NO. 1	UNSIZED	-	2070	2.78	0.21%	SLIGHT LAMINATION
12	22.2%	MIX NO. 1	UNSIZED	-	2070	2.48	3.87%	
13	15%	MIX NO. 1	UNSIZED	-	2090	2.63	0.72%	
14	15%	MIX NO. 1	-200, +325 MESH	-	2090	2.65	1.08%	
15	15%	MIX NO. 1	-100, +325 MESH	-	2090	2.73	2.36%	
16	15%	MIX NO. 1	-200 MESH	-	2090	2.74	0	
17	15%	MIX NO. 1	-325 MESH	-	2090	2.75	0	
18	15%	MIX NO. 1	-325 MESH	100% $\alpha$ -SIC	2090	2.80	0	

FIG. 2



50X

(a) T.B. #11, 16wt % UNSIZED 10042 GRAPHITE, 50X

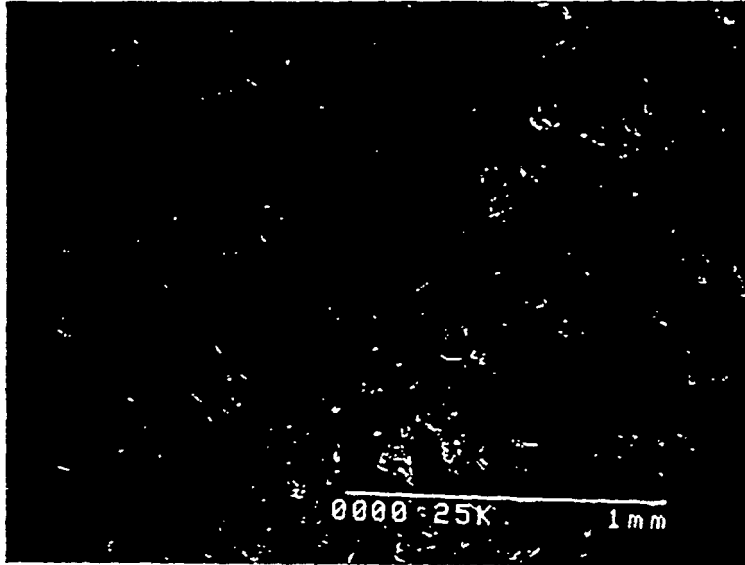
### *FIG. 3*



50X

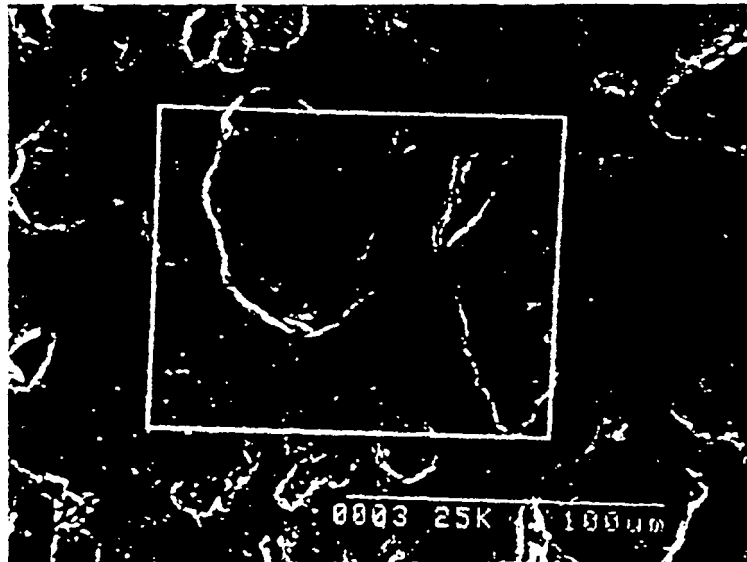
(b) T.B. #17, 15wt % 10042 GRAPHITE, -325 MESH, 50X

### *FIG. 4*



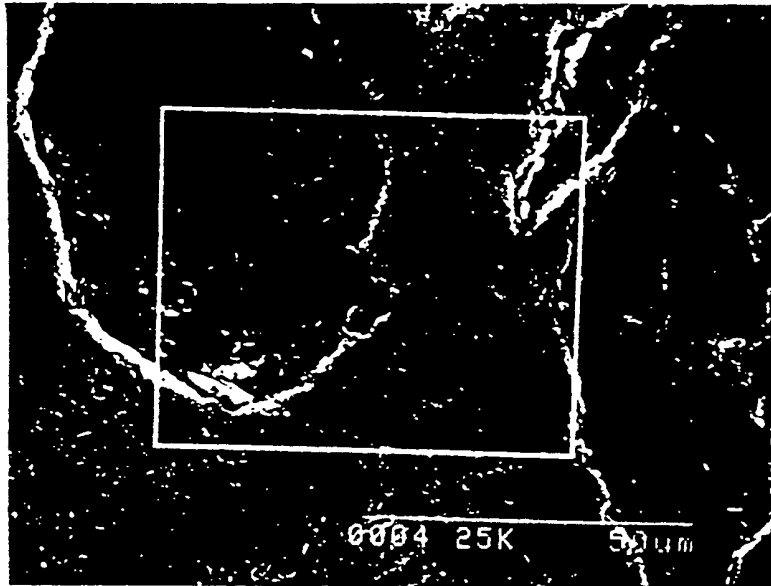
50X

*FIG. 5A*



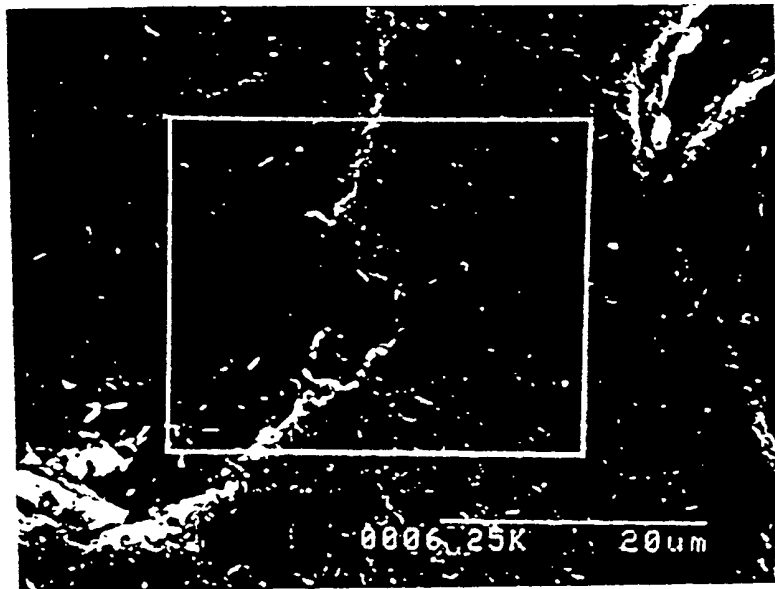
500X

*FIG. 5B*



1000 X

*FIG. 5C*



2000 X

*FIG. 5D*